

Power Rectifier MURHD560T4G, MURHD560W1T4G,

Features and Benefits

- Ultrafast 30 Nanosecond Recovery Times
- 175°C Operating Junction Temperature
- High Temperature Glass Passivated Junction
- High Voltage Capability to 600 Volts
- SURHD8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Supplies
- Inverters
- Free Wheeling Diodes

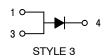
Mechanical Characteristics

- · Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 0.4 g (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Ratings:
 - ♦ Machine Model = C (> 400 V)
 - ♦ Human Body Model = 3B (> 8000 V)

ULTRAFAST RECTIFIER 5.0 AMPERES 600 VOLTS

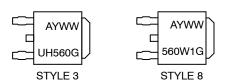


DPAK CASE 369C STYLES 3, 8





MARKING DIAGRAM



UH560 = MURHD560T4 560W1 = MURHD560W1T4 A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping [†]
MURHD560T4G	DPAK (Pb-Free)	2500 / Tape & Reel
MURHD560W1T4G	DPAK (Pb-Free)	2500 / Tape & Reel
SSURHD8560W1T4G	DPAK (Pb-Free)	2500 / Tape & Reel

DISCONTINUED (Note 1)

1

SURHD8560T4G	DPAK (Pb-Free)	2500 / Tape & Reel
SURHD8560W1T4G	DPAK (Pb-Free)	2500 / Tape & Reel
SSURHD8560T4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

MURHD560T4G, MURHD560W1T4G,

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	600	V
Average Rectified Forward Current (Rated V _R , T _C = 159°C)	I _{F(AV)}	5.0	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	50	Α
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance, Junction to Case	$R_{ heta JC}$	2.5	°C/W
Maximum Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	49.5	°C/W

^{1.} Rating applies when surface mounted on a 1.5 mm FR4 PC board with a 1 oz. thick, 700 mm² Cu area.

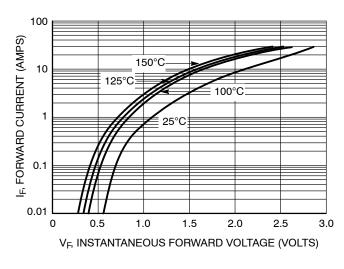
ELECTRICAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 5.0 \text{ Amps}, T_C = 25^{\circ}\text{C}$) ($I_F = 5.0 \text{ Amps}, T_C = 125^{\circ}\text{C}$)	V _F	2.7 1.65	٧
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T _C = 25°C) (Rated dc Voltage, T _C = 125°C)	I _R	10 70	μА
Maximum Reverse Recovery Time (I _F = 1.0 Amp, di/dt = 50 Amps/μs, V _R = 30 V, T _J = 25°C)	t _{rr}	30	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

MURHD560T4G, MURHD560W1T4G,



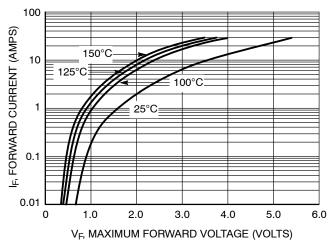


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

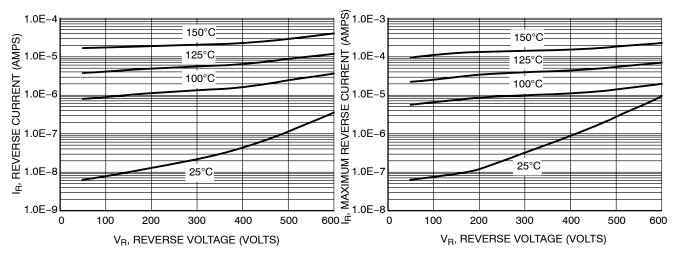


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

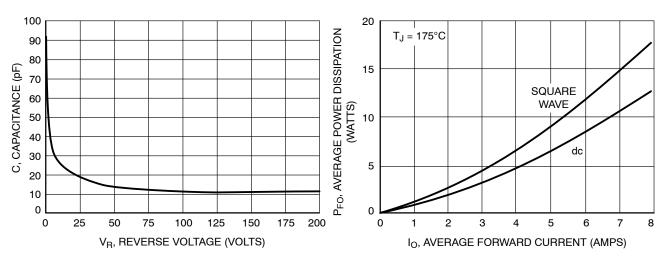


Figure 5. Typical Capacitance

Figure 6. Forward Power Dissipation

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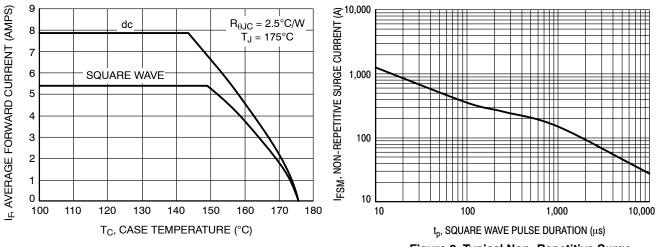


Figure 7. Current Derating

Figure 8. Typical Non-Repetitive Surge Current

^{*} Typical performance based on a limited sample size. ON Semiconductor does not guarantee ratings not listed in the Maximum Ratings table.

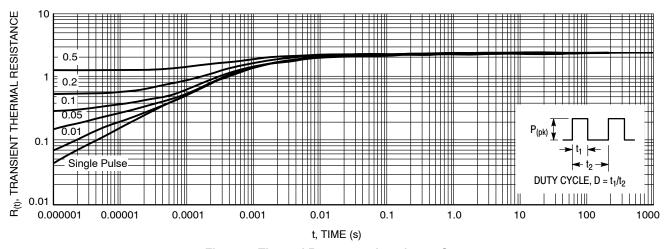


Figure 9. Thermal Response, Junction to Case

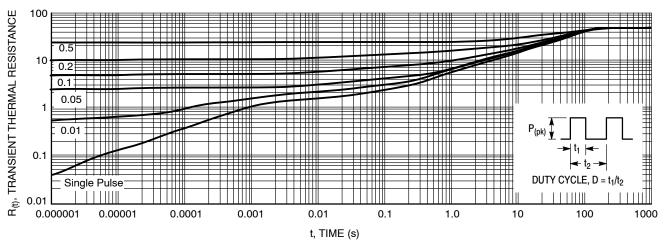
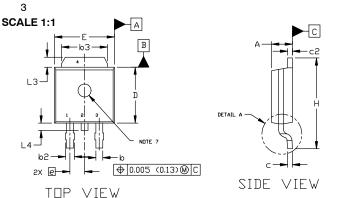


Figure 10. Thermal Response, Junction to Ambient

DPAK (SINGLE GAUGE)

CASE 369C ISSUE G

DATE 31 MAY 2023

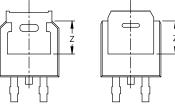


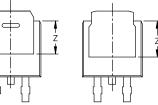


- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE DUTERMOST EXTREMES OF THE PLASTIC BODY.

 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INC	HES	MILLIM	ETERS
MIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
ھ	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
Ū	0.018	0.024	0.46	0.61
-2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29 BSC	
Η	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 B2C		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040	-	1.01
Z	0.155		3.93	

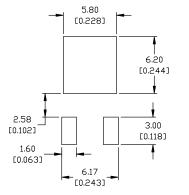


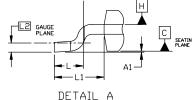


BOTTOM VIEW

BOTTOM VIEW

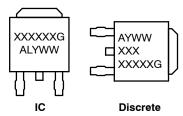
ALTERNATE CONSTRUCTIONS





CW ROTATED 90°

GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT* *FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

S

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
COLLECTOR	DRAIN	CATHODE	ANODE	ANODE
EMITTER	SOURCE	ANODE	3. GATE	CATHODE
COLLECTOR	4. DRAIN	CATHODE	ANODE	ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 6: STYLE 8: STYLE 9: STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE 3 FMITTER 3 RESISTOR ADJUST 3 GATE 4. COLLECTOR 4. CATHODE 4. ANODE 4. CATHODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

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